



SEMITOP[®] 2

IGBT Module

SK45GB063

SK45GAL063

SK45GAR063

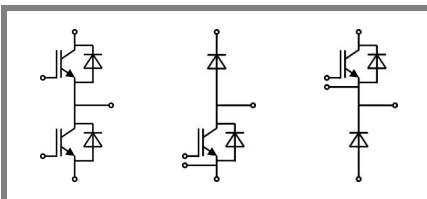
Preliminary Data

Features

- Compact design
- One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- N channel, homogeneous Silicon structure (NPT-Non punchthrough IGBT)
- High short circuit capability
- Low tail current with low temperature dependence
- UL recognized, file no. E63532

Typical Applications

- Switching (not for linear use)
- Inverter
- Switched mode power supplies
- UPS



GB

GAL

GAR

Absolute Maximum Ratings				$T_s = 25\text{ °C}$, unless otherwise specified	
Symbol	Conditions			Values	Units
IGBT					
V_{CES}	$T_j = 25\text{ °C}$			600	V
I_C	$T_j = 125\text{ °C}$	$T_s = 25\text{ °C}$		45	A
		$T_s = 80\text{ °C}$		30	A
I_{CRM}	$I_{CRM} = 2 \times I_{Cnom}$			100	A
V_{GES}				± 20	V
t_{psc}	$V_{CC} = 300\text{ V}$; $V_{GE} \leq 20\text{ V}$; $T_j = 125\text{ °C}$ $V_{CES} < 600\text{ V}$			10	μs

Inverse Diode					
I_F	$T_j = 150\text{ °C}$	$T_s = 25\text{ °C}$		57	A
		$T_s = 80\text{ °C}$		38	A
I_{FRM}					A
I_{FSM}	$t_p = 10\text{ ms}$; half sine wave	$T_j = 150\text{ °C}$		440	A
Freewheeling Diode					
I_F	$T_j = 150\text{ °C}$	$T_s = 25\text{ °C}$		57	A
		$T_s = 80\text{ °C}$		38	A
I_{FRM}					A
I_{FSM}	$t_p = 150\text{ ms}$;	$T_j = \text{ °C}$		440	A
Module					
$I_{t(RMS)}$					A
T_{vj}				-40 ... +150	$^{\circ}\text{C}$
T_{stg}				-40 ... +125	$^{\circ}\text{C}$
V_{isol}	AC, 1 min.			2500	V

Characteristics			T _s = 25 °C, unless otherwise specified			
Symbol	Conditions		min.	typ.	max.	Units
IGBT						
V _{GE(th)}	V _{GE} = V _{CE} , I _C = 1 mA		4,5	5,5	6,5	V
I _{CES}	V _{GE} = 0 V, V _{CE} = V _{CES}	T _J = 25 °C T _J = 125 °C			0,15	mA mA
I _{GES}	V _{CE} = 0 V, V _{GE} = 30 V	T _J = 25 °C T _J = 125 °C			120	nA nA
V _{CE0}		T _J = 25 °C T _J = 125 °C		1 1,1		V V
r _{CE}	V _{GE} = 15 V	T _J = 25°C T _J = 125°C		20		mΩ mΩ
V _{CE(sat)}	I _{Cnom} = 50 A, V _{GE} = 15 V	T _J = 25°C _{chiplev.} T _J = 125°C _{chiplev.}		2,1	2,5	V V
C _{ies} C _{oes} C _{res}	V _{CE} = 25, V _{GE} = 0 V	f = 1 MHz		2,2 0,2		nF nF nF
Q _G	V _{GE} = 0 ... 20 V			155		nC
t _{d(on)} t _r E _{on}	R _{Gon} = 22 Ω	V _{CC} = 300V I _C = 30A		45 35 1,4		ns ns mJ
t _{d(off)} t _f E _{off}	R _{Goff} = 22 Ω	T _J = 125 °C V _{GE} = ±15V		250 25 1,2		ns ns mJ
R _{th(j-s)}	per IGBT				1	K/W



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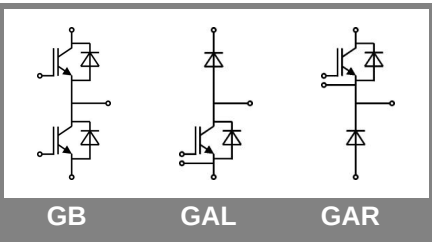
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Typical Applications

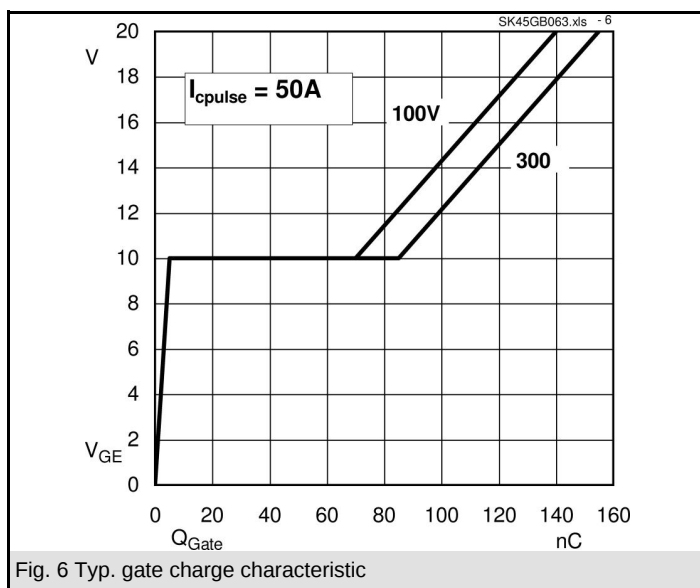
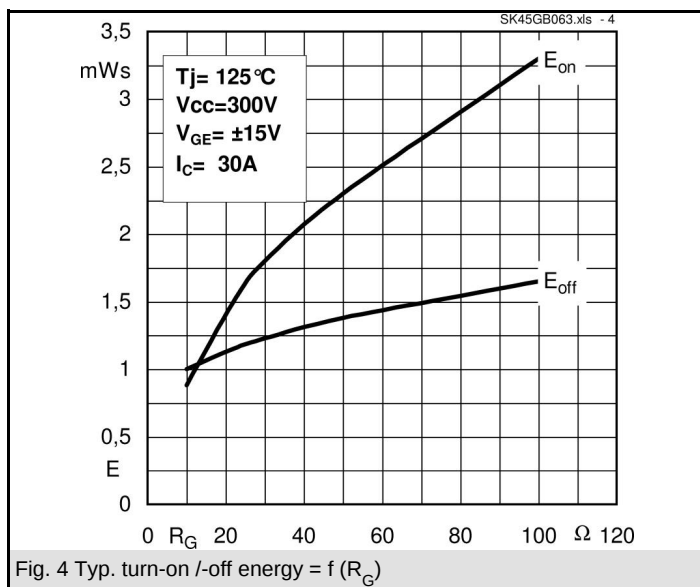
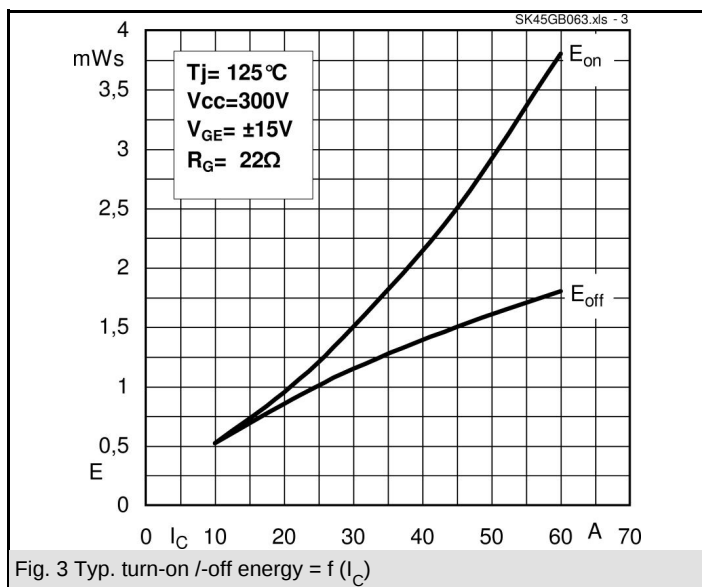
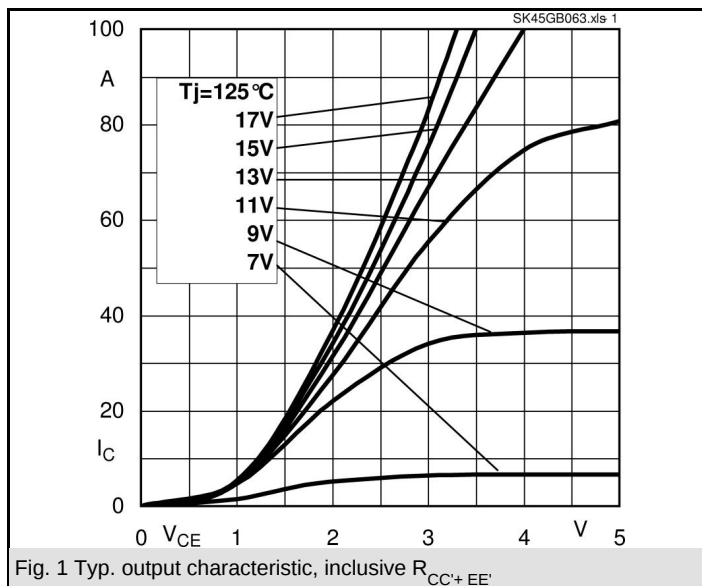
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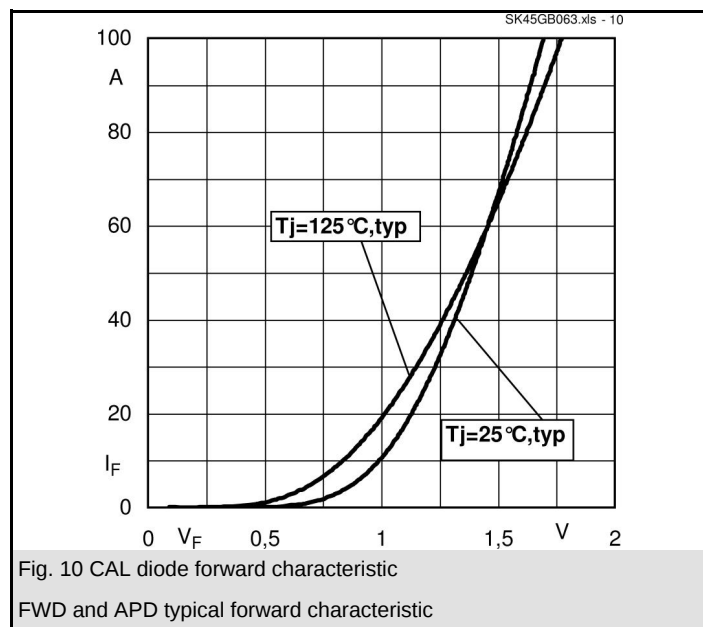
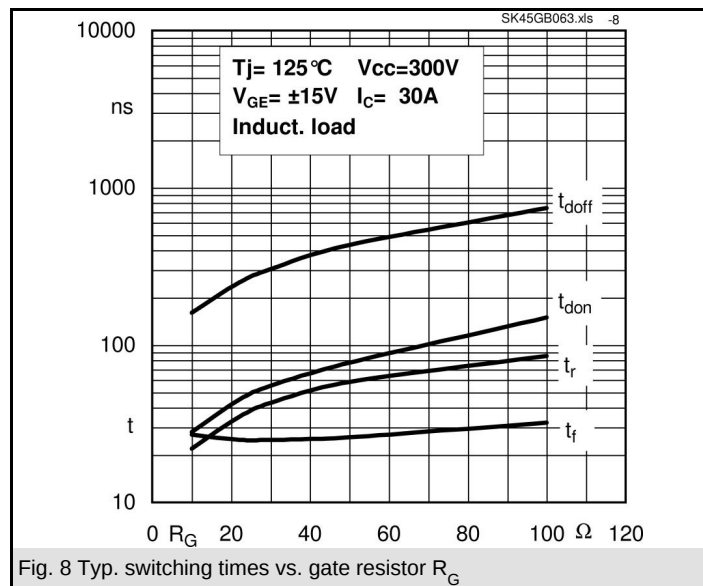
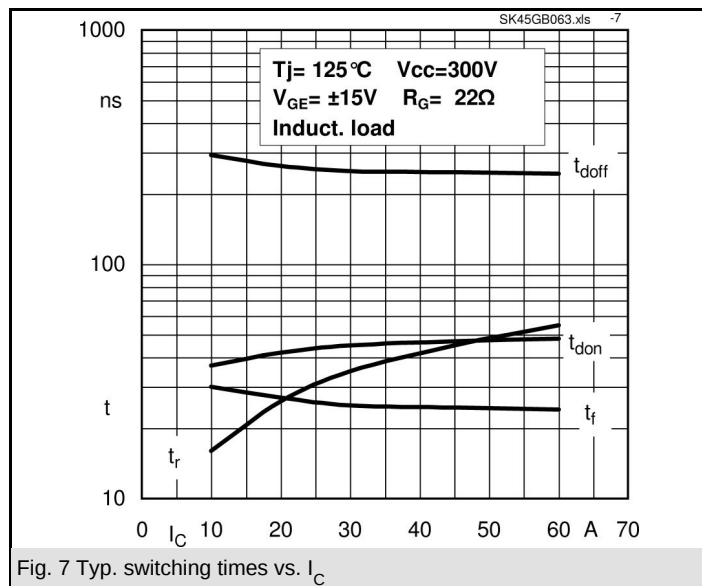


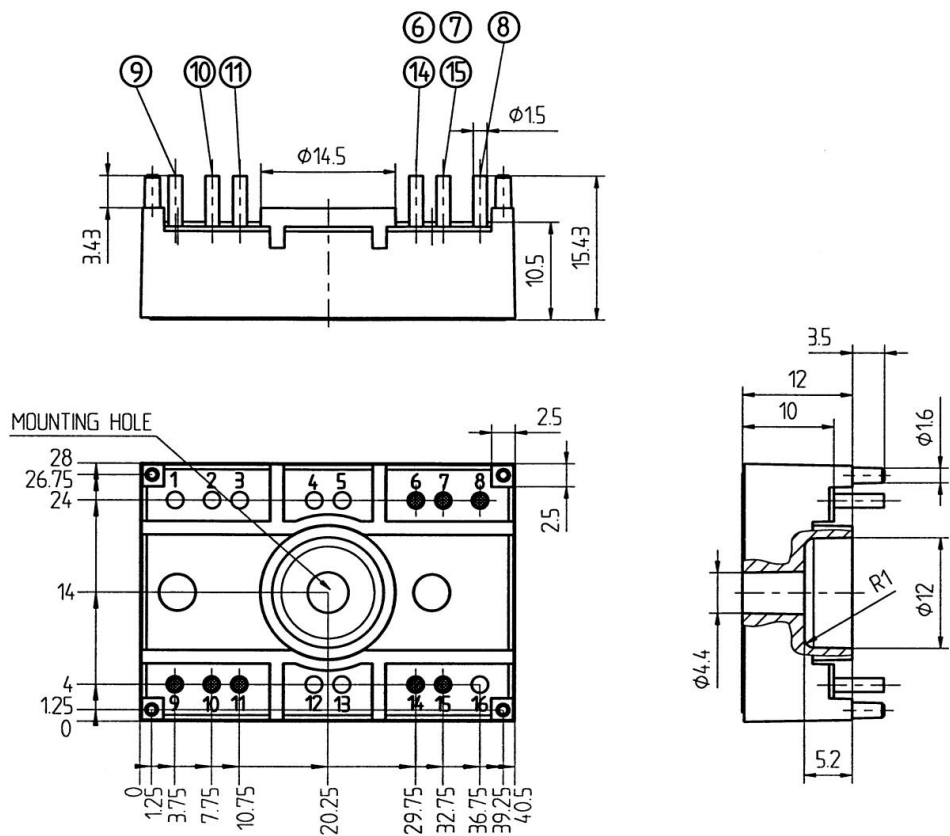
Characteristics					
Symbol	Conditions	min.	typ.	max.	Units
Inverse Diode					
$V_F = V_{EC}$	$I_{Fnom} = 30\text{ A}; V_{GE} = 0\text{ V}$		$T_j = 25\text{ }^{\circ}\text{C}_{chiplev.}$	1,45	V
			$T_j = 125\text{ }^{\circ}\text{C}_{chiplev.}$	1,7	V
V_{F0}			$T_j = 125\text{ }^{\circ}\text{C}$	0,85	V
r_F			$T_j = 125\text{ }^{\circ}\text{C}$	9	mΩ
I_{RRM}	$I_F = 30\text{ A}$		$T_j = 125\text{ }^{\circ}\text{C}$	16	A
Q_{rr}	$di/dt = -500\text{ A/}\mu\text{s}$			2	μC
E_{rr}	$V_{CC}=300\text{ V}$			0,25	mJ
$R_{th(j-s)D}$	per diode			1,2	K/W
Freewheeling Diode					
$V_F = V_{EC}$	$I_{Fnom} = 30\text{ A}; V_{GE} = 0\text{ V}$		$T_j = 25\text{ }^{\circ}\text{C}_{chiplev.}$	1,45	V
			$T_j = 125\text{ }^{\circ}\text{C}_{chiplev.}$	1,7	V
V_{F0}			$T_j = 125\text{ }^{\circ}\text{C}$	0,85	V
r_F			$T_j = 125\text{ }^{\circ}\text{C}$	9	V
I_{RRM}	$I_F = 30\text{ A}$		$T_j = 125\text{ }^{\circ}\text{C}$	16	A
Q_{rr}	$di/dt = -500\text{ A/}\mu\text{s}$			2	μC
E_{rr}	$V_{CC}=300\text{ V}$			0,25	mJ
$R_{th(j-s)FD}$	per diode			1,2	K/W
M_s	to heat sink			2	Nm
w				19	g

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.







Case T4 (Suggested hole diameter, in the PCB, for solder pins and plastic mounting pins: 2mm)

